

Vishay Siliconix

RoHS

COMPLIANT

N-Channel 75-V (D-S) MOSFET

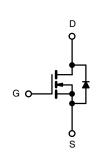
PRODUCT SUMMARY			
V _{DS} (V)	R_{DS(on)} (Ω)	I _D (A)	Q _g (Typ.)
75	0.0068 at V_{GS} = 10 V	90 ^d	75

FEATURES

- TrenchFET[®] Power MOSFET
- 175 °C Junction Temperature
- 100 % R_g and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

- Power Supply
- Secondary Synchronous Rectification
- Industrial



N-Channel MOSFET

٦	FO-	22(DAB	3
		0)	
	G		s	J

Top View Ordering Information: SUP90N08-6m8P-E3 (Lead (Pb)-free)

ABSOLUTE MAXIMUM RATINGS	$T_{\rm C}$ = 25 °C, unless oth	erwise noted			
Parameter		Symbol	Limit	Unit	
Drain-Source Voltage		V _{DS}	75	v	
Gate-Source Voltage		V _{GS}	± 22	v	
Continuous Drain Current (T _J = 175 °C)	T _C = 25 °C	L_	90 ^d	A	
	T _C = 70 °C	I _D	90 ^d		
Pulsed Drain Current		I _{DM}	240		
Avalanche Current		I _{AS}	50		
Single Avalanche Energy ^a	L = 0.1 mH	E _{AS}	125	mJ	
	T _C = 25 °C	Р	272 ^b	w	
Maximum Power Dissipation ^a	T _A = 25 °C ^c		3.75	V	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C	

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	0.55	- °C/W	

Notes:

b. See SOA curve for voltage derating.c. When Mounted on 1" square PCB (FR-4 material).

d. Package limited.

a. Duty cycle \leq 1 %.

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V, I_D = 250 \mu A$	75			V	
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2.5		4.5	v	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 250	nA	
		$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}$			1		
Zero Gate Voltage Drain Current	I _{DSS}	$V_{DS} = 75 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$			50	μΑ	
		$V_{DS} = 75 \text{ V}, V_{GS} = 0 \text{ V}, T_{J} = 150 \text{ °C}$			250		
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 10 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	70			А	
	D	V _{GS} = 10 V, I _D = 20 A		0.0056	0.0068	0	
Drain-Source On-State Resistance ^a	R _{DS(on)}	V_{GS} = 10 V, I _D = 20 A, T _J = 125 °C		0.009	0.011	Ω	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 20 A		50		S	
Dynamic ^b	•			•			
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 30 V, f = 1 MHz		4620		pF	
Output Capacitance	C _{oss}			517			
Reverse Transfer Capacitance	C _{rss}			247			
Total Gate Charge ^c	Qg			75	115	nC	
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 30 \text{ V}, \text{ V}_{GS} = 10 \text{ V}, \text{ I}_{D} = 50 \text{ A}$		25.5			
Gate-Drain Charge ^c	Q _{gd}			20			
Gate Resistance	Rg	f = 1 MHz		1.2	2.4	Ω	
Turn-On Delay Time ^c	t _{d(on)}			16	30		
Rise Time ^c	t _r	$V_{\text{DD}} = 30 \text{ V}, \text{ R}_{\text{L}} = 0.6 \Omega$ $\text{I}_{\text{D}} \cong 50 \text{ A}, \text{ V}_{\text{GEN}} = 10 \text{ V}, \text{ R}_{\text{g}} = 1 \Omega$		11	20	20	
Turn-Off Delay Time ^c	t _{d(off)}			24	40	ns	
Fall Time ^c	t _f			10	20		
Source-Drain Diode Ratings and Cha	aracteristics 7	$\Gamma_{\rm C} = 25 \ ^{\circ}{\rm C}^{\rm b}$					
Continuous Current	ا _S				85	^	
Pulsed Current	I _{SM}				240	A	
Forward Voltage ^a	V _{SD}	I _F = 20 A, V _{GS} = 0 V		0.83	1.5	V	
Reverse Recovery Time	t _{rr}			60	100	ns	
Peak Reverse Recovery Current	I _{RM(REC)}	I _F = 75 A, dl/dt = 100 A/μs		3.3	4.5	А	
Reverse Recovery Charge	Q _{rr}			100	150	nC	

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %. b. Guaranteed by design, not subject to production testing.

c. Independent of operating temperature.

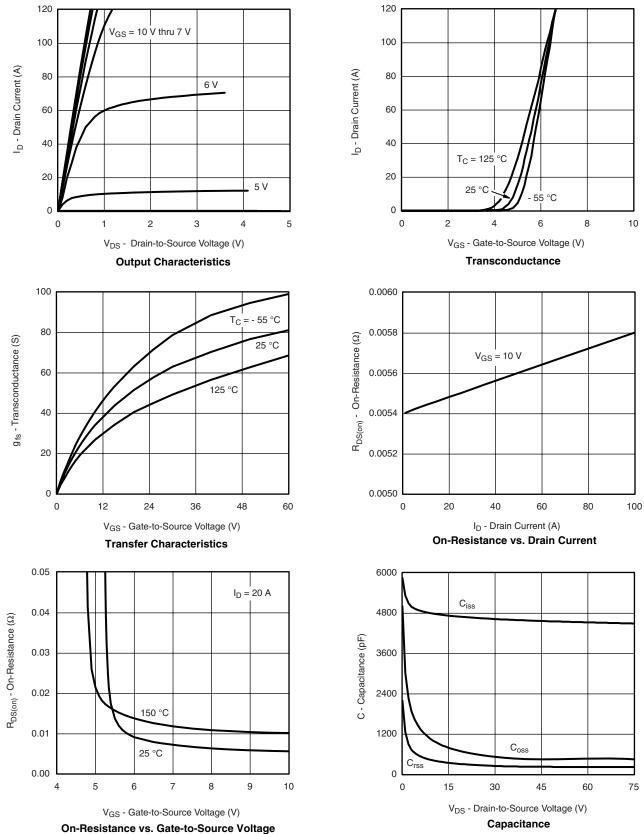
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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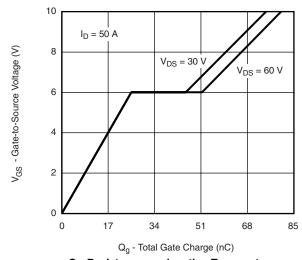
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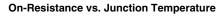


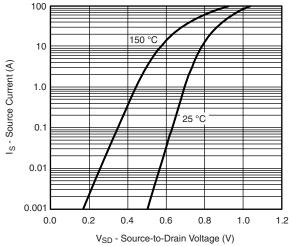


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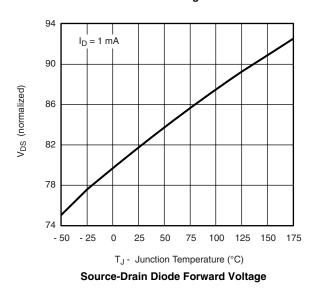
TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted

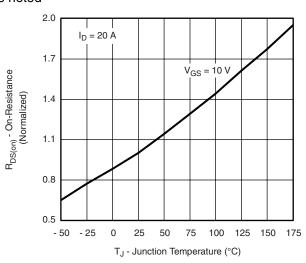






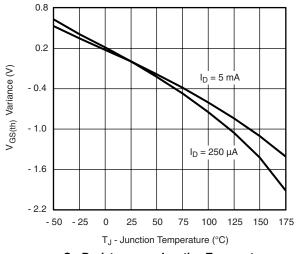




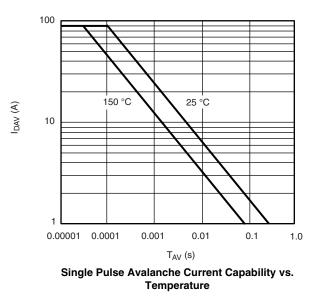


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On-Resistance vs. Junction Temperature

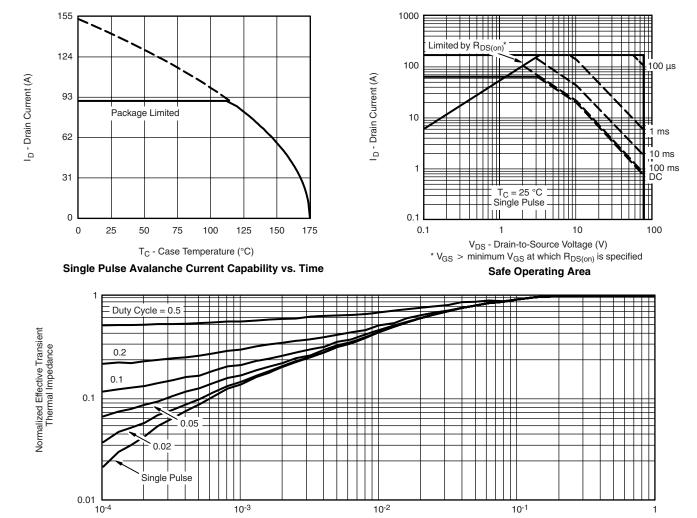


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Square Wave Pulse Duration (s) Normalized Thermal Transient Impedance, Junction-to-Case

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